

Triacs

logic level

BT136 series D

GENERAL DESCRIPTION

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

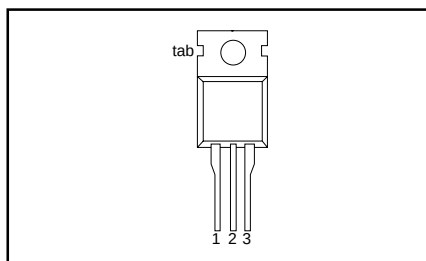
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	600D 600	V
$I_{\text{T(RMS)}}$	RMS on-state current	4	A
I_{TSM}	Non-repetitive peak on-state current	25	A

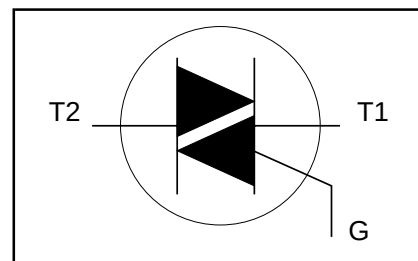
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-600D 600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 107^\circ\text{C}$	-	4	A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25^\circ\text{C}$ prior to surge	-	25	A
		$t = 20\text{ ms}$	-	27	A
		$t = 16.7\text{ ms}$	-	3.1	A ² s
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-		
di_{T}/dt	Repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-		
		T2+ G+	-	50	A/ μs
		T2+ G-	-	50	A/ μs
		T2- G-	-	50	A/ μs
		T2- G+	-	10	A/ μs
I_{GM}	Peak gate current		-	2	A
V_{GM}	Peak gate voltage		-	5	V
P_{GM}	Peak gate power		-	5	W
$P_{\text{G(AV)}}$	Average gate power	over any 20 ms period	-	0.5	W
T_{stg}	Storage temperature		-40	150	$^\circ\text{C}$
T_{j}	Operating junction temperature		-	125	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$	Thermal resistance junction to mounting base	full cycle	-	-	3.0	K/W
		half cycle	-	-	3.7	K/W
$R_{\text{th j-a}}$	Thermal resistance junction to ambient	in free air	-	60	-	K/W

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STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$				
		T2+ G+	-	2.0	5	mA
		T2+ G-	-	2.5	5	mA
		T2- G-	-	2.5	5	mA
		T2- G+	-	5.0	10	mA
I_L	Latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$				
		T2+ G+	-	1.6	10	mA
		T2+ G-	-	4.5	15	mA
		T2- G-	-	1.2	10	mA
		T2- G+	-	2.2	15	mA
I_H	Holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	1.2	10	mA
V_T	On-state voltage	$I_T = 5\text{ A}$	-	1.4	1.70	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^{\circ}\text{C}$	0.25	0.4	-	V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ }^{\circ}\text{C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

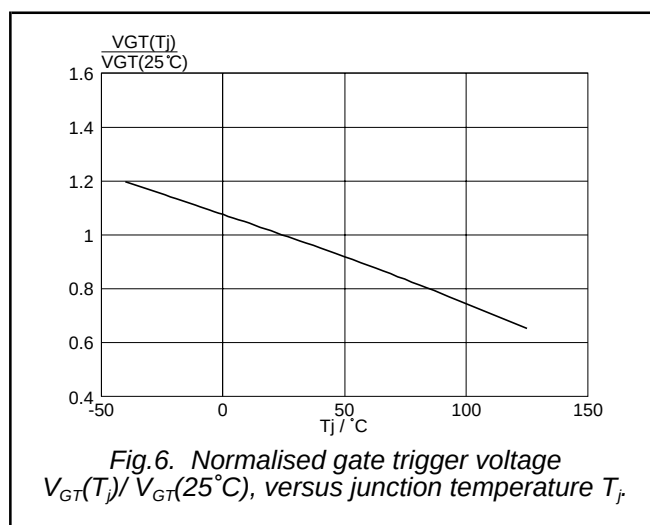
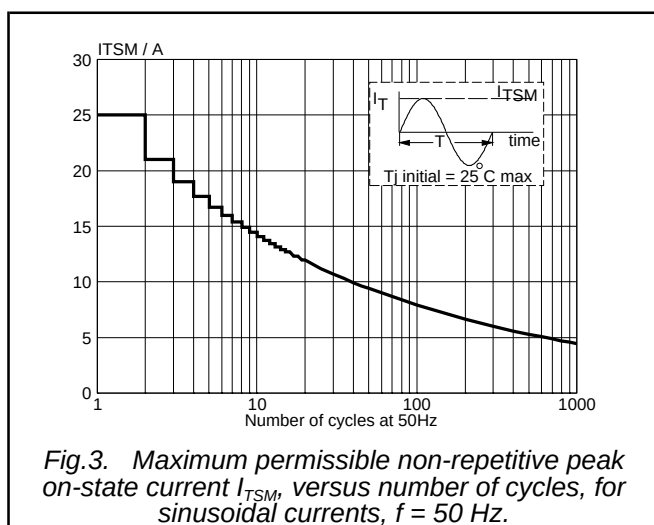
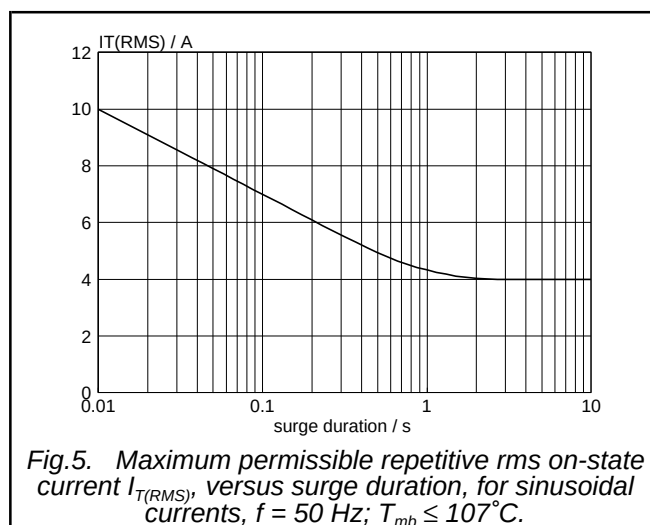
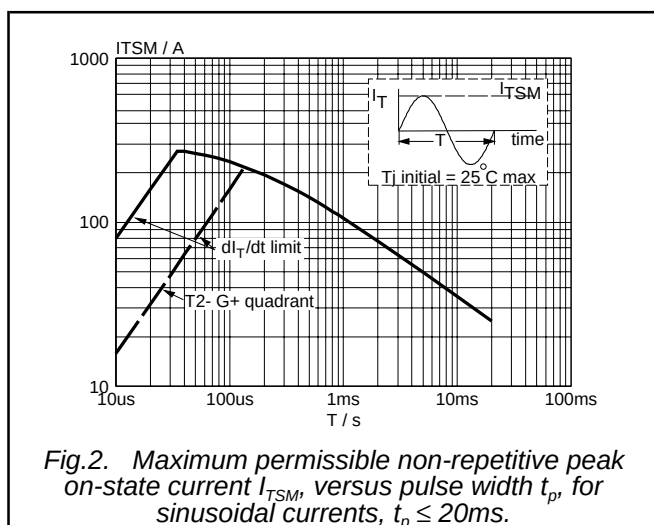
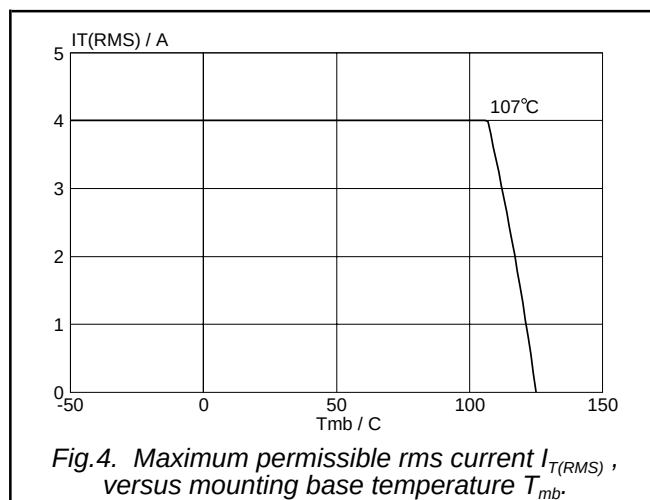
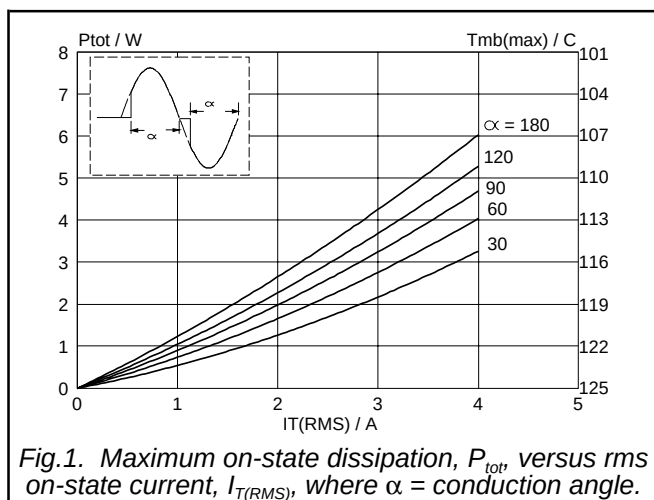
$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ }^{\circ}\text{C}$; exponential waveform; $R_{GK} = 1\text{ k}\Omega$	-	5	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 6\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

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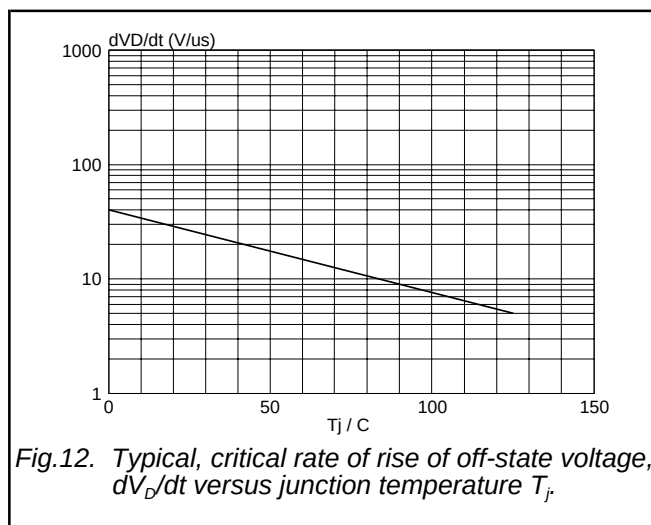
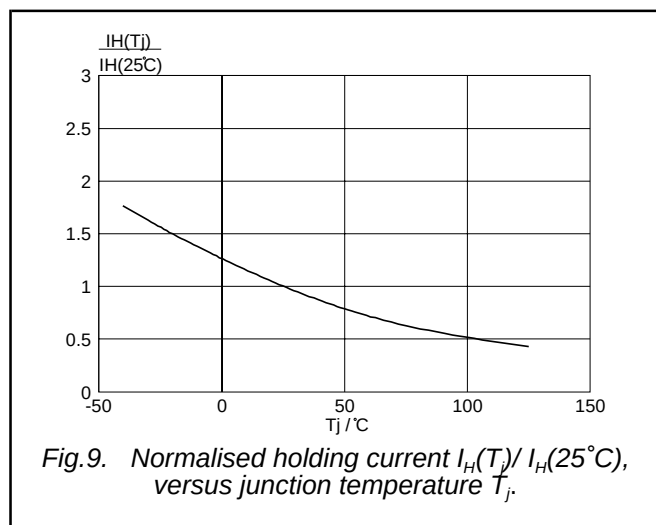
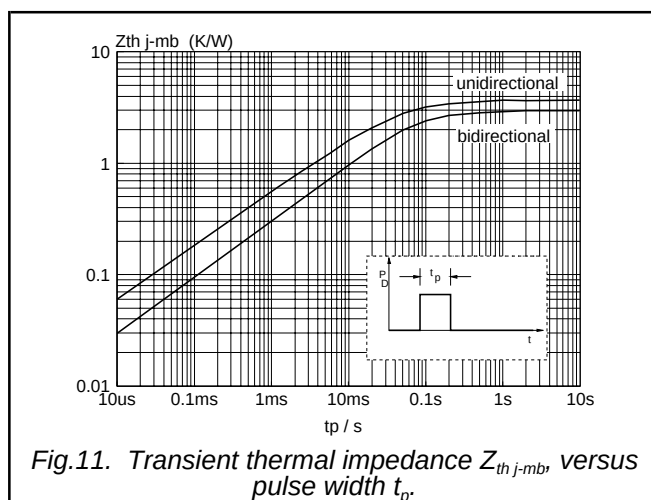
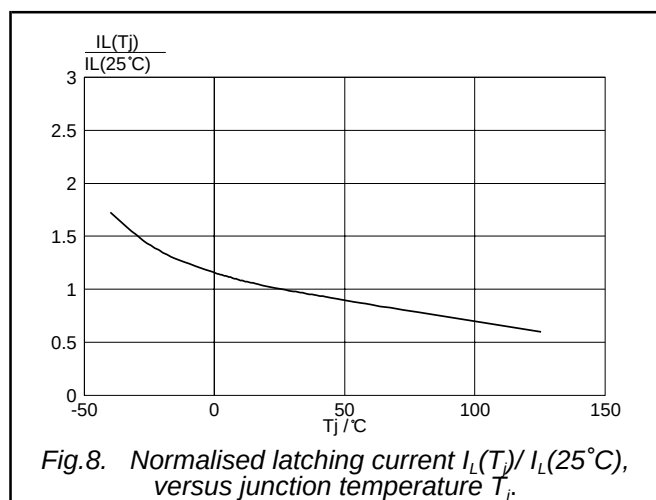
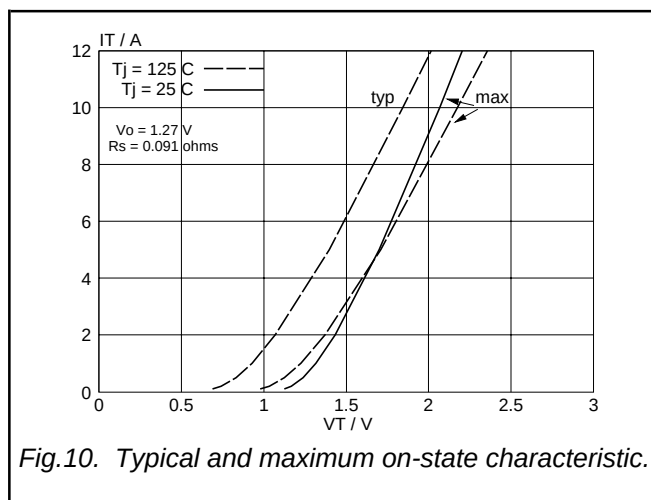
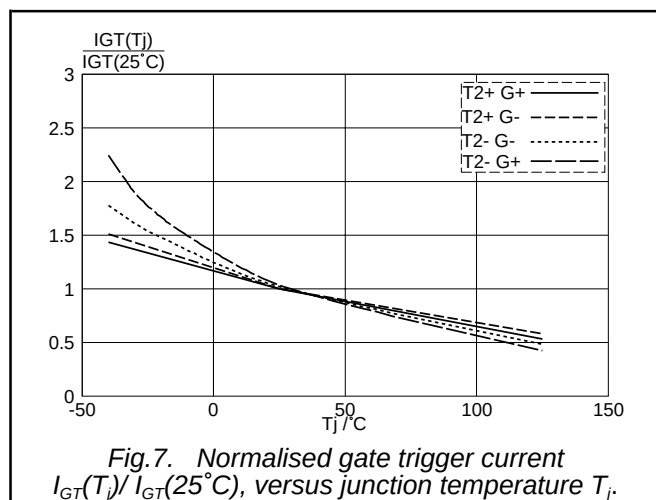
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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

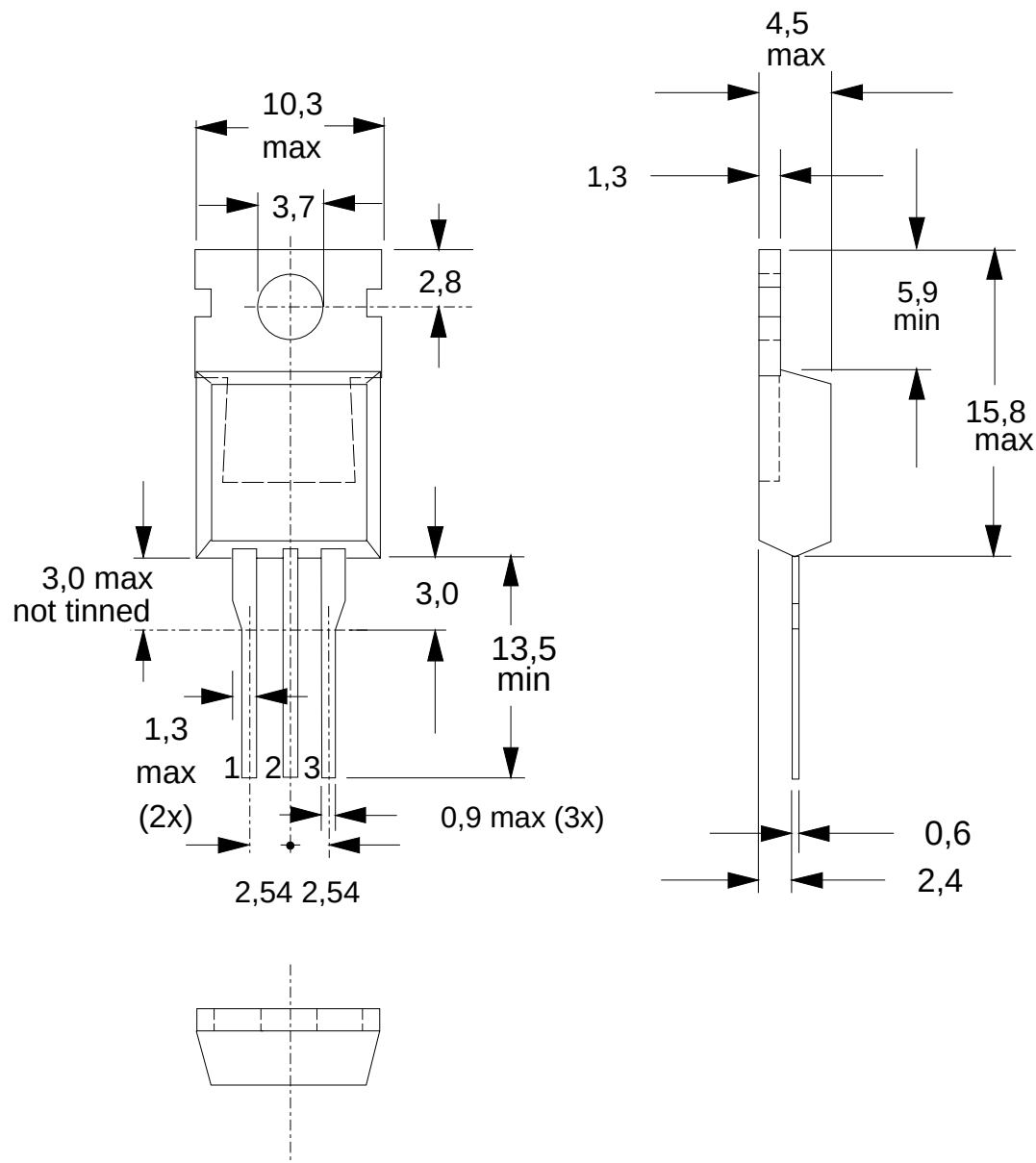


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

DATA SHEET STATUS		
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A
Limiting values		
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		
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